

## **The Data Book Project**

DatasheetArchive.com has launched an ambitious effort to digitize thousands of obsolete data books and technical manuals, making them searchable via the DatasheetArchive website.

**Scroll down to see the scanned document.**

# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										外形	備考		
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>ie</sub>	h <sub>re</sub>	h <sub>oe</sub>	f <sub>αb</sub>			C <sub>ob</sub>	r <sub>bb'</sub>
									I <sub>CE</sub> (V)	I <sub>C</sub> (mA)	V <sub>CE</sub> (V)	I <sub>E</sub> (mA)	h <sub>FE</sub> *	h <sub>ie</sub> *	h <sub>re</sub> *	h <sub>oe</sub> *	f <sub>αb</sub> *	C <sub>ob</sub>	r <sub>bb'</sub>			
1	2	3	4	5					6		7				8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>T</sub>.
- 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)						電 気 的 特 性 (T <sub>a</sub> = 25°C)										外 形	備 考							
				V <sub>CB0</sub> (V)	V <sub>EB0</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値		直流又はパルス hFE		バイアス		h <sub>fe</sub> h <sub>fe</sub> *	h <sub>ie</sub> h <sub>ie</sub> *	h <sub>re</sub> h <sub>re</sub> *	h <sub>oe</sub> h <sub>oe</sub> *	f <sub>ob</sub> f <sub>ob</sub> *			C <sub>ob</sub> (pF)	r <sub>bb</sub> r <sub>bb</sub> (real)*					
									(μA)	V <sub>CB</sub> (V)	V <sub>CE</sub> (V)	I <sub>C</sub> (mA)	V <sub>CB</sub> (V)	I <sub>E</sub> (mA)										h <sub>fe</sub> *	h <sub>ie</sub> * (Ω)	h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> * (μΩ)	f <sub>T</sub> * (Mc)
★ 2SC769	三 菱	PA. SW	Si. TMe	120	5	10A	50 W (T <sub>c</sub> =25°C)	150	1mA	30	25	4	2 A										102					
★ "	"	"	"	200	5	10A	50 W (T <sub>c</sub> =25°C)	150	1mA	30	25	4	2 A										102					
★ "	"	"	"	250	5	10A	50 W (T <sub>c</sub> =25°C)	150	1mA	30	25	4	2 A										102					
★ "	三 洋	RF. Conv. Mix. Osc.	Si. EP	15		30	120	125	1	10	60	6	1	6	-1						300*	1.5	C <sub>c</sub> r <sub>bb</sub> 30pS	27				
★ "	三 菱	Osc	"	50	5	200	250	125	1	25				6	-10	60	P <sub>oss</sub> = 40mW (f = 27MHz)							138B				
★ "	"	PA	"	50	4	500	680	175	10	30	70	10	100				P <sub>oss</sub> = 70mW (f = 27MHz, V <sub>ce</sub> = 12V, I <sub>c</sub> = 25mA)							84B				
★ "	"	"	"	75	4	1 A	800	200	10	30	70	10	100				P <sub>o</sub> = 0.7W (f = 27MHz, V <sub>ce</sub> = 12V, P <sub>i</sub> = 30mW)							84B				
★ "	"	"	"	75	4	1 A	1 W	200	10	30	70	10	100				P <sub>o</sub> = 1.5W (f = 27MHz, V <sub>ce</sub> = 12V, P <sub>i</sub> = 75mW)							84B				
★ "	"	"	"	75	4	1 A	2 W	200	10	30	50	10	100				P <sub>o</sub> = 3.5W (f = 27MHz, V <sub>ce</sub> = 12V, P <sub>i</sub> = 0.4W)							97B				
★ "	"	"	"	80	4	2 A	2.5W	200	10	30	50	10	100				P <sub>o</sub> = 4W (f = 27MHz, V <sub>ce</sub> = 12V, P <sub>i</sub> = 0.4W)							97B				
★ "	東 芝	SW	Si. TMe	300	6	2 A	25 W (T <sub>c</sub> =25°C)	150	100	200	30~200	10	100	10	-100						20*	40		99				
★ "	"	RF	Si. EP	70	2	20	150	125	5	70				10	-2	60	I <sub>on</sub> < 2 μS, t <sub>off</sub> < 4 μS						100*	3	50	33	2SA429 ヒコソフリ	
★ "	日 電	RF. PA	Si. E	75	5	1 A	5 W (T <sub>c</sub> =25°C)	175	1	40	80	10	150	10	-150	80							350*	11	13*	84B		
★ "	東 芝	PA	Si. TMe	300	5	1.5A	20 W (T <sub>c</sub> =25°C)	150	100	200	30~240	10	100	10	-100								10*	50	25	99		
★ "	"	"	"	200	5	1.5A	20 W (T <sub>c</sub> =25°C)	150	100	200	30~240	10	100	10	-100								10*	50	25	99		
★ "	784	RF	Si. EP	40	4	20	100	125	0.5	18	25~140	6	1	6	-1								500*	C <sub>re</sub> 0.65	C <sub>c</sub> r <sub>bb</sub> 10pS	33		
★ "	"	Conv. Mix Osc	"	40	4	20	100	125	0.5	18	25~140	6	1	6	-1								500*	C <sub>re</sub> 0.65	C <sub>c</sub> r <sub>bb</sub> 10pS	33		
★ "	786	RF	"	20	3	20	200	150	0.05	10	20~200	5	4	10	-4								NF = 3.5dB (f = 100MHz)	> 250*	C <sub>re</sub> 0.25-0.55	< 25	50C	
★ "	787	RF. LN	Si. P	25	3	20	150	150	0.025	10	> 25	10	2	10	-2								NF = 5dB (f = 800MHz)	1000*	C <sub>re</sub> 0.3		50C	
★ "	788	RF. SW	Si. T	250	5	50	800	150	0.1	30	25~240	5	10	30	-10								120*	4	25	84B		
★ "	789	RF. PA	Si. T	70	5	4 A	30W (T <sub>c</sub> =25°C)	150	30	50	40~240	5	500	5	-500								> 3*	150		268		
★ "	790	PA	"	50	5	3 A	25 W (T <sub>c</sub> =25°C)	150	10	30	40~240	2	500	2	-500								10*	85		268	2SA450 ヒコソフリ	
★ "	791	"	Si. TMe	90	5	1.5A	15 W (T <sub>c</sub> =25°C)	150	10	30	40~250	2	200	5	-500								20	40		99		
★ "	792	"	"	300	5	1.5A	50 W (T <sub>c</sub> =25°C)	150	50	300	30~250	10	300	10	-100								10*	80		102		
★ "	793	"	Si. TMe	100	5	7 A	60 W (T <sub>c</sub> =25°C)	150	1mA	30	30~200	5	1 A	5	-500								9*	220		102		
★ "	794	"	"	70	5	7 A	60 W (T <sub>c</sub> =25°C)	150	1mA	30	50	5	1 A	5	-500	50							9*	230	15	102		
★ "	795	ソニー	Si. DB	250	6	100	9 W (T <sub>c</sub> =25°C)	150	10	100	70	10	10	10	-10	70							180*	7	C <sub>c</sub> r <sub>bb</sub> 50pS	100		
★ "	796	富士通	RF. Osc	40		500	1 W (T <sub>c</sub> =25°C)	175	5	12	50	4	150	20	-15								230*	5	20*	84B		
★ "	797	PA	"	60		500	1 W (T <sub>c</sub> =25°C)	175	5	12	30	4	150	20	-15								P <sub>o</sub> = 1.3W (f = 27Mc, V <sub>ce</sub> = 12V, P <sub>i</sub> = 75mW)	150*	5	12*	84B	
★ "	798	"	Si. TP	60		1.5A	5 W (T <sub>c</sub> =25°C)	175	5	12	70	4	400										P <sub>o</sub> = 3.5W (f = 27Mc, V <sub>ce</sub> = 12V, P <sub>i</sub> = 0.5W)				84B	